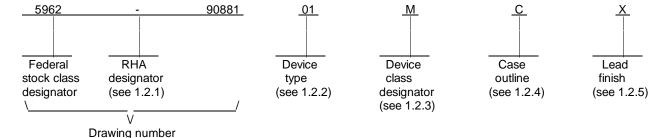
LTR								F	REVIS	IONS										
					С	ESCF	RIPTIO	N					DATE (YR-MO-DA)			DA)	APPROVED			
А	spec	Make change to input offset voltage test and supply of specified under table I. Make change to table IIC. In N.O.R. 5962-R348-92.									ith	92-11-25			M. A. FRYE					
В	curre	Delete outline letter G and case outline A-1. Make ch current test as specified under table I. In accordance R264-94.										94-08-18			M. A. FRYE			Ē		
С				s 04, 09 and tab)9. Ma	ake ch	anges	to 1.3,	ı		96-1	0-08			R. M	NINNC	١
REV SHEET REV	C	С																		
SHEET	C 15	C 16																		
SHEET REV SHEET REV STAT	15 US			RE ¹	V		С	С	С	С	С	С	С	С	С	С	С	С	С	С
SHEET REV SHEET	15 US				V EET		C 1	C 2	C 3	C 4	C 5	C 6	C 7	C 8	C 9	C 10	C 11	C 12	C 13	C 14
SHEET REV SHEET REV STAT OF SHEET PMIC N/A	15 US S	16		SHI							5	6	7 NSE S	8 SUPPL	9 -Y CE	10	11	12	13	
SHEET REV SHEET REV STAT OF SHEET PMIC N/A STA MICR	15 US S ANDA OCIR	RD CUI	T	SHI PRE RIC	PARED CK OFF	FICER	1			4	5	6 DEFEI	7 NSE S COL	8 SUPPL UMBL	9 LY CE JS, OI	10 NTER	11 COLU 3216	12	13	14
SHEET REV SHEET REV STAT OF SHEET PMIC N/A STA MICR DR THIS DRAW FOR	15 US S ANDA OCIR AWING IS A USE BY	RD CUI' IG		SHI PRE RIG CHE RA	EET PAREE CK OFF CKED JESH	BY PITHAI	1 DIA			4 MIC PRE	5 I	6 DEFEI	7 NSE S COL	8 SUPPL UMBU	9 LY CE JS, OH	10 NTER HIO 4:	11	12	13	14 ER,
SHEET REV SHEET REV STAT OF SHEET PMIC N/A STA MICR DR THIS DRAW FOR	ANDA OCIR AWIN VING IS A USE BY PARTMEN ENCIES	RD CUI' IG VAILA ALL JTS OF THE	BLE	SHI PRE RIG CHE RA	PAREICK OFF	BY PITHAI D BY D MON	1 DIA	2		4 MIC PRE	5 ROCI ECISIO CON	6 DEFEI	7 NSE S COL	8 SUPPL UMBU	9 LY CE JS, OH	10 NTER HIO 4:	COLU 3216 EED, I	12 JMBUS LOW MONG	13 POWI	ER,
SHEET REV SHEET REV STAT OF SHEET PMIC N/A STA MICR DR THIS DRAW FOR AND AG DEPARTM	ANDA OCIR AWIN VING IS A USE BY PARTMEN ENCIES	RD CUI' IG VAILA ALL JTS OF THE	BLE	SHI PRE RIG CHE RA APPI RA	PAREICK OFF	BY PITHAI D BY D MON	DIA NININ DVAL E 10-10	2		4 MIC PRE SILI	5 ROCI ECISIO CON	RCUI DN, O	7 NSE S COL	8 SUPPLUMBU	9 LY CE JS, OH	10 NTER HIO 4:	11 COLU 3216	12 JMBUS LOW MONG	13 POWI	ER,

- 1. SCOPE
- 1.1 <u>Scope</u>. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.
 - 1.2 PIN. The PIN is as shown in the following example:



- 1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.
 - 1.2.2 <u>Device type(s)</u>. The device type(s) identify the circuit function as follows:

Device type	Generic number	<u>Circuit function</u>
01	TLE2021M	High speed low power precision single operational amplifier
02	TLE2022M	High speed low power precision dual operational amplifier
03	TLE2024M	High speed low power precision quad operational amplifier
04	TLE2021AM	High speed low power precision single operational amplifier
05 06	TLE2022AM	High speed low power precision dual operational amplifier
06	TLE2024AM	High speed low power precision quad operational amplifier
07	TLE2021BM	High speed low power precision single operational amplifier
08	TLE2022BM	High speed low power precision dual operational amplifier
09	TLE2024BM	High speed low power precision quad operational amplifier

1.2.3 <u>Device class designator</u>. The device class designator is a single letter identifying the product assurance level as follows:

Device class	Device requirements documentation
М	Vendor self-certification to the requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A
Q or V	Certification and qualification to MIL-PRF-38535

1.2.4 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
С	GDIP1-T14 or CDIP2-T14	14	Dual-in-line
G	MACY1-X8	8	Can
Р	GDIP1-T8 or CDIP2-T8	8	Dual-in-line
2	CQCC1-N20	20	Square leadless chip carrier

1.2.5 <u>Lead finish</u>. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

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1.3 Absolute maximum ratings. 1/2/

Supply volatge (+ V_{CC}) Supply volatge (- V_{CC}) Differential input voltage $\underline{3}$ / Input voltage range (V_{I}) (any input) Input current (I_{I}) (each input) Output current (I_{O}):	-20 V dc ±0.6 V dc ±V _{CC}
Device types 01, 04, 07	±20 mA
Device types 02, 05, 08	±30 mA
Device types 03, 06, 09	
Total current into +V _{CC} terminal:	
Device types 01, 04, 07	20 mA
Device types 02, 03, 05, 06, 08, 09	
Total current into -V _{CC} terminal:	
Device types 01, 04, 07	20 mA
Device types 02, 03, 05, 06, 08, 09	80 mA
Duration of short circuit current at (or below) +25°C 4/	Unlimited
Storage temperature range	-65° C to +150° C
Terminal temperature for 60 seconds:	
Case 2	+260° C
Lead temperature, soldering 6 mm (1/16 inch) from	
case for 60 seconds:	
Cases C, G, and P	+300° C
Junction temperature	+150°C
Power dissipation (P _D)	
Cases 2 and C <u>5</u> /	1375 mW
Case G <u>5</u> /	650 mW
Case P <u>5</u> /	
Thermal resistance, junction-to-case (Θ_{JC})	See MIL-STD-1835

1.4 Recommended operating conditions.

- 1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.
- $\underline{2}$ / All voltage values, except differential voltages, are with respect to the midpoint between +V_{CC} and -V_{CC}.
- 3/ Differential voltages are at the noninverting input with respect to the inverting input. Excessive current will flow if a differential input voltage in excess of approximately ±600 mV is applied between the inputs unless some limiting resistance is used.
- 4/ The output may be shorted to either supply. Temperature and supply voltage must be limited to ensure that the maximum dissipation rating is not exceeded.
- 5/ Above +25° C derate at a factor of 11.0 mW/° C for cases C and 2, 5.2 mW/° C for case G, and 8.4 mW/° C for case P.

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2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standards, and handbooks</u>. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solicitation.

SPECIFICATION

MILITARY

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

STANDARDS

MILITARY

MIL-STD-883 - Test Methods and Procedures for Microelectronics.

MIL-STD-973 - Configuration Management. MIL-STD-1835 - Microcircuit Case Outlines.

HANDBOOKS

MILITARY

MIL-HDBK-103 - List of Standard Microcircuit Drawings (SMD's).

MIL-HDBK-780 - Standard Microcircuit Drawings.

(Unless otherwise indicated, copies of the specification, standards, and handbooks are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.
 - 3.2.1 Case outline(s). The case outline(s) shall be in accordance with 1.2.4 herein.
 - 3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.
 - 3.2.3 Test circuits. The test circuits shall be as specified on figure 2.
- 3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.

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Test	Symbol	Conditions	Group A	Device	Limits		Unit
		-55°C ≤ T _A ≤+125°C unless otherwise specified	subgroups	type	Min	Max	
Input offset voltage	V _{IO}	$V_{CC} = \pm 2.5 \text{ V}, V_{IC} = 0 \text{ V},$	1	01		600	μV
		$V_0 = 0 \text{ V, R}_S = 50 \Omega$	2,3			1100	
		$V_{CC} = \pm 15 \text{ V}, V_{IC} = 0 \text{ V}, V_{O} = 0 \text{ V}, R_{S} = 50 \Omega$	1			500	
		$V_0 = 0 \text{ V, R}_S = 50 \Omega$	2,3			1000	
		$V_{CC} = \pm 2.5 \text{ V}, V_{IC} = 0 \text{ V}, V_{O} = 0 \text{ V}, R_{S} = 50 \Omega$	1	02		600	μV
		$V_0 = 0 \text{ V}, R_S = 50 \Omega$	2,3			800	
		$V_{CC} = \pm 15 \text{ V}, V_{IC} = 0 \text{ V}, V_{O} = 0 \text{ V}, R_{S} = 50 \Omega$	1			500	
		$V_0 = 0 \text{ V, R}_S = 50 \Omega$	2,3			700	
		$V_{CC} = \pm 2.5 \text{ V}, V_{IC} = 0 \text{ V}, V_{O} = 0 \text{ V}, R_{S} = 50 \Omega$	1	03		1100	μV
		$V_0 = 0 \text{ V}, R_S = 50 \Omega$	2,3			1300	
		$V_{CC} = \pm 15 \text{ V}, V_{IC} = 0 \text{ V}, V_{O} = 0 \text{ V}, R_{S} = 50 \Omega$	1			1000	
			2,3			1200	
		$V_{CC} = \pm 2.5 \text{ V}, V_{IC} = 0 \text{ V}, V_{O} = 0 \text{ V}, R_{S} = 50 \Omega$	1	04		300	μV
			2,3			600	
		$V_{CC} = \pm 15 \text{ V}, V_{IC} = 0 \text{ V}, V_{O} = 0 \text{ V}, R_{S} = 50 \Omega$	1			200	
			2,3			500	
		$V_{CC} = \pm 2.5 \text{ V}, V_{IC} = 0 \text{ V}, V_{O} = 0 \text{ V}, R_{S} = 50 \Omega$	1	05		400	μV
			2,3			550	
		$V_{CC} = \pm 15 \text{ V}, V_{IC} = 0 \text{ V}, V_{O} = 0 \text{ V}, R_{S} = 50 \Omega$	1			300	
		$V_0 = 0 \text{ V, R}_S = 50 \Omega$	2,3			450	
		$V_{CC} = \pm 2.5 \text{ V}, V_{IC} = 0 \text{ V}, V_{O} = 0 \text{ V}, R_{S} = 50 \Omega$	1	06		850	μV
		$V_0 = 0 \text{ V, R}_S = 50 \Omega$	2,3			1050	
		$V_{CC} = \pm 15 \text{ V}, V_{IC} = 0 \text{ V}, V_{O} = 0 \text{ V}, R_{S} = 50 \Omega$	1			750	
		$v_0 = 0 \text{ v, } \kappa_S = 50 \Omega$	2,3			950	
		$V_{CC} = \pm 2.5 \text{ V}, V_{IC} = 0 \text{ V}, V_{O} = 0 \text{ V}, R_{S} = 50 \Omega$	1	07		200	μV
		$v_0 = 0 \text{ v, } \kappa_S = 50 \Omega$	2,3			300	
		$V_{CC} = \pm 15 \text{ V}, V_{IC} = 0 \text{ V}, V_{O} = 0 \text{ V}, R_{S} = 50 \Omega$	1			100	
		$v_0 = 0 \text{ v, } \kappa_S = 50 \Omega$	2,3			200	

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TABLE I. <u>Electrical performance characteristics</u> - Continued.

Test	Symbol	Conditions	Group A	Device	Limits		Unit
		-55°C ≤ T _A ≤+125°C unless otherwise specified	subgroups	type	Min	Max	
Input offset voltage	V _{IO}	$V_{CC} = \pm 2.5 \text{ V}, V_{IC} = 0 \text{ V}, V_{O} = 0 \text{ V}, R_{S} = 50 \Omega$	1	08		250	μV
		$V_0 = 0 \text{ V}, R_S = 50 \Omega$	2,3			400	
		$V_{CC} = \pm 15 \text{ V}, V_{IC} = 0 \text{ V}, V_{O} = 0 \text{ V}, R_{S} = 50 \Omega$	1			150	
		$V_0 = 0 \text{ V}, R_S = 50 \Omega$	2,3			300	
		$V_{CC} = \pm 2.5 \text{ V}, V_{IC} = 0 \text{ V}, V_{O} = 0 \text{ V}, R_{S} = 50 \Omega$	1	09		600	μV
		$V_0 = 0 \text{ V}, R_S = 50 \Omega$	2,3			800	
		$V_{CC} = \pm 15 \text{ V}, V_{IC} = 0 \text{ V}, V_{O} = 0 \text{ V}, R_{S} = 50 \Omega$	1			500	
		$V_0 = 0 \text{ V}, R_S = 50 \Omega$	2,3			700	
Input offset current	I _{IO}	$V_{CC} = 5 \text{ V or } \pm 15 \text{ V},$ $V_{IC} = 0 \text{ V}, R_S = 50 \Omega$	1	01,04, 07		3	nA
		$V_{IC} = 0 \text{ V}, R_S = 50 \Omega$	2,3			5	
			1,2,3	02		5	nA
			1	03		6	nA
			2,3			10	
			1	05		4	nA
			2,3			5	
			1	06		5	nA
			2,3			9	
			1	08		3	nA
			2,3			5	
			1	09		4	nA
			2,3			8	
Input bias current	I _{IB}	$V_{CC} = 5 \text{ V or } \pm 15 \text{ V}, \\ V_{IC} = 0 \text{ V, R}_{S} = 50 \Omega$	1,2,3	01		70	nA
		$V_{IC} = 0.01, K_S = 50.72$	1,2,3	02		70	nA
			1	03		70	nA
			2,3			90	
			1,2,3	04		65	nA

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TABLE I. <u>Electrical performance characteristics</u> - Continued.

Test	Symbol	Conditions	Group A	Device	Lin	nits	Unit
		-55°C ≤ T _A ≤+125°C unless otherwise specified	subgroups	type	Min	Max	
Input bias current	I _{IB}	$V_{CC} = 5 \text{ V or } \pm 15 \text{ V},$ $V_{IC} = 0 \text{ V}, R_S = 50 \Omega$	1	05		65	nA
		$V_{IC} = 0 \text{ V, R}_{S} = 50 \Omega$	2,3			70	
			1	06		65	nA
			2,3			85	
			1,2,3	07		60	nA
			1	08		60	nA
			2,3			70	
			1	09		60	nA
			2,3			80	
Common mode input voltage range	V _{ICR}	$V_{CC} = \pm 15 \text{ V}, R_S = 50 \Omega$	1,2,3	All	-15 to 13.2		V
	$V_{CC} = 5 \text{ V}, R_S = 50 \Omega$	1,2,3		0 to 3.2		V	
Maximum positive peak	+V _{OM}	$V_{CC} = \pm 15 \text{ V}, R_{L} = 10 \text{ k}\Omega$	4	01,04,	14.0		V
output voltage swing			5,6	07	13.8		
			4	02,05,	14.0		V
			5,6	08	13.9		
			4	03	13.8		V
			5,6		13.7		
			4	06	13.9		V
			5,6		13.7		
			4	09	14		V
			5,6		13.8		
Maximum negative peak	-V _{OM}	$V_{CC} = \pm 15 \text{ V}, R_L = 10 \text{ k}\Omega$	4	All	-13.7		V
output voltage swing			5,6		-13.6		

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	TABLE	I. Electrical performan	ice chara	cteristics	- Cont	tinued.			
Test	Symbol	Conditions -55°C ≤ T _A ≤+12	5°C	Group subgro		Device type	Lim	nits	Unit
		-55°C ≤ T _A ≤+12 unless otherwise spe	ecified		•	,,	Min	Max	
High level output voltage	V _{ОН}	$V_{CC} = 5 \text{ V}, R_{L} = 10 \text{ I}$	kΩ	1		01,02, 04,05,	4.0		V
				2,3		07,08	3.8		
				1		03,06	3.9		V
				2,3			3.7		
				1		09	4		V
				2,3			3.8		
Low level output voltage	V _{OL}	$V_{CC} = 5 \text{ V}, R_L = 10 \text{ I}$	kΩ	1		All		0.8	V
				2,3				0.95	
Large signal differential	A_{VD}	$V_{CC} = 5 \text{ V}, R_{L} = 10 \text{ V}$ $V_{O} = 1.4 \text{ V} \text{ to 4 V}$	kΩ	4		01,02,	0.3		V/µV
voltage amplification		V _O = 1.4 V to 4 V		5,6		04,07	0.1		
				4		03	0.2		V/µV
				5,6			0.1		
				4		05	0.4		V/µV
				5,6			0.1		
				4		06	0.3		V/µV
				5,6			0.1		
				4		08	0.5		V/µV
				5,6			0.1		
				4		09	0.4		V/µV
				5,6			0.1		
	$V_{CC} = \pm 15 \text{ V}, R_{L} = 10 \text{ k}\Omega$ $V_{O} = \pm 10 \text{ V}$	0 kΩ	4		01,04,	1.0		V/µV	
		$V_O = \pm 10 \text{ V}$		5,6		07	0.5		
				4,5,6	6	02	0.8		V/µV
				4,5,6	6	03	0.4		V/µV
				4,5,6	6	05	1.0		V/µV
				4,5,6	6	06	0.8		V/µV
				4,5,6	6	08	1.5		V/µV
				4,5,6	6	09	1.0		V/µV
See footnotes at end of table.									
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TABLE I. <u>Electrical performance characteristics</u> - Continued.

Test	Symbol Conditions		Group A	Device	Lir	mits	Unit
	-55°C ≤ T _A ≤+125°C subgroups unless otherwise specified		subgroups	type	Min	Max	
Common mode rejection		1	01,04,	85		dB	
ratio		V _{IC} = V _{ICR} min	2,3	07	80]
		$V_{CC} = \pm 15 \text{ V}, R_S = 50 \Omega$	1		100		
		V _{IC} = V _{ICR} min	2,3		96		
		$V_{CC} = 5 \text{ V}, R_{S} = 50 \Omega$	1	02	85		dB
		V _{IC} = V _{ICR} min	2,3		80		
		$V_{CC} = \pm 15 \text{ V}, R_S = 50 \Omega$	1		95]
		V _{IC} = V _{ICR} min	2,3		91		
		$V_{CC} = 5 \text{ V}, R_{S} = 50 \Omega$ $V_{IC} = V_{ICR} \text{ min}$	1,2,3	03	80		dB
		$V_{CC} = \pm 15 \text{ V}, R_S = 50 \Omega$	1		92		
		V _{IC} = V _{ICR} min	2,3		88		
		$V_{CC} = 5 \text{ V}, R_S = 50 \Omega$	1	05	87		dB
		V _{IC} = V _{ICR} min	2,3		82		
	$V_{CC} = \pm 15 \text{ V}, R_S = 50 \Omega$	$V_{CC} = \pm 15 \text{ V}, R_S = 50 \Omega$	1		97		
		V _{IC} = V _{ICR} min	2,3		93		
		$V_{CC} = 5 \text{ V}, R_S = 50 \Omega$ $V_{IC} = V_{ICR} \text{ min}$	1,2,3	06	82		dB
		$V_{CC} = \pm 15 \text{ V}, R_{S} = 50 \Omega$	1		94		
		V _{IC} = V _{ICR} min	2,3		90		
		$V_{CC} = 5 \text{ V}, R_{S} = 50 \Omega$ $V_{IC} = V_{ICR} \text{ min}$	1	08	90	<u> </u>	dB
		VIC = VICR MIII	2,3	ļ	85		
		$V_{CC} = \pm 15 \text{ V}, R_S = 50 \Omega$	1	ļ	100		
		V _{IC} = V _{ICR} min	2,3		96		
		V_{CC} = 5 V, R_S = 50 Ω V_{IC} = V_{ICR} min	1,2,3	09	85		dB
		$V_{CC} = \pm 15 \text{ V}, R_S = 50 \Omega$	1		97]
		V _{IC} = V _{ICR} min	2,3	'	93		

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	TABLE	I. Electrical performance chara	acteristics - Con	itinued.				
Test	Test Symbol Conditions		Group A	Device	Liı	mits	Unit	
		-55°C ≤ T _A ≤+125°C unless otherwise specified	subgroups	type	Min	Max		
Supply voltage rejection	$\begin{array}{ccc} \text{ion} & k_{\text{SVR}} & V_{\text{CC}} = 5 \text{ V}, \\ V_{\text{CC}} = 5 \text{ V to } 30 \text{ V} \end{array}$		1	01,04,	105		dB	
ratio ($\Delta V_{CC} / \Delta V_{IO}$)		$V_{CC} = 5 \text{ V to } 30 \text{ V}$	2,3	07	100			
			1	02	100		dB	
			2,3		95			
			1	03	98		dB	
			2,3		93			
			1	05	103		dB	
			2,3		98			
			1	06	100		dB	
			2,3		95			
			1	08	105		dB	
		2,3		100				
			1	09	103		dB	
	2,3	2,3		98				
		$V_{CC} = \pm 15 \text{ V},$ $V_{CC} = \pm 2.5 \text{ V to } \pm 15 \text{ V}$	1	01,04, 07	105		dB	
		VCC - 12.5 V to 115 V	= ±2.5 V t0 ±15 V 2,3	07	100			
			1	02	100		dB	
			2,3		95			
			1	03	98		dB	
			2,3		93			
			1	05	103		dB	
			2,3		98			
			1	06	100		dB	
			2,3		95			
			1	08	105		dB	
			2,3		100			
					1	09	103	
			2,3		98			

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TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	Conditions	Group A	Device	Lir	mits	Unit
		-55°C ≤ T _A ≤+125°C unless otherwise specified	subgroups	type	Min	Max	
Supply current	I _{CC}	V _{CC} = 5 V, V ₀ = 2.5 V, no load	1,2,3	01,04, 07		230	μА
			1,2,3	02,05, 08		600	μА
			1,2,3	03,06, 09		1200	μА
		$V_{CC} = \pm 15 \text{ V},$ $V_0 = 0 \text{ V}, \text{ no load}$	1,2,3	01,04, 07		300	μА
			1,2,3	02,05, 08		700	μА
			1,2,3	03,06, 09		1400	μА
Slew rate at unity gain 1/	SR	$V_{CC} = \pm 15 \text{ V}, V_{O} = \pm 10 \text{ V}$	4	All	0.45		V/µs
			5,6		0.4		

1/ See figure 2.

- 3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked as listed in MIL-HDBK-103. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.
- 3.5.1 <u>Certification/compliance mark</u>. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.
- 3.6 <u>Certificate of compliance</u>. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 <u>Notification of change for device class M.</u> For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-973.
- 3.9 <u>Verification and review for device class M</u>. For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

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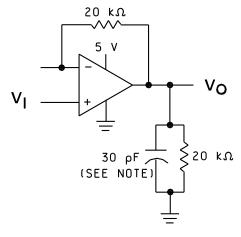
Device type	01,0	4,07	02,0	5,08	03,0	6,09		
Case outlines	G and P	2	G and P	2	С	2		
Terminal number		Terminal symbol						
1	OFFSET N1	NC	OUTPUT 1	NC	OUTPUT 1	NC		
2	-INPUT	OFFSET N1	-INPUT 1	OUTPUT 1	-INPUT 1	OUTPUT 1		
3	+INPUT	NC	+INPUT 1	NC	+INPUT 1	-INPUT 1		
4	-V _{CC} /GND	NC	-V _{CC} /GND	NC	+V _{CC}	+INPUT 1		
5	OFFSET N2	-INPUT	+INPUT 2	-INPUT 1	+INPUT 2	NC		
6	OUTPUT	NC	-INPUT 2	NC	-INPUT 2	+V _{CC}		
7	+V _{CC}	+INPUT	OUTPUT 2	+INPUT 1	OUTPUT 2	NC		
8	NC	NC	+V _{CC}	NC	OUTPUT 3	+INPUT 2		
9		NC		NC	-INPUT 3	-INPUT 2		
10		-V _{CC} /GND		-V _{CC} /GND	+INPUT 3	OUTPUT 2		
11		NC		NC	-V _{CC} /GND	NC		
12		OFFSET N2		+INPUT 2	+INPUT 4	OUTPUT 3		
13		NC		NC	-INPUT 4	-INPUT 3		
14		NC		NC	OUTPUT 4	+INPUT 3		
15		OUTPUT		-INPUT 2		NC		
16		NC		NC		-V _{CC} /GND		
17		+V _{CC}		OUTPUT 2		NC		
18		NC		NC		+INPUT 4		
19		NC		NC		-INPUT 4		
20		NC		+V _{CC}		OUTPUT 4		

NC = No connection

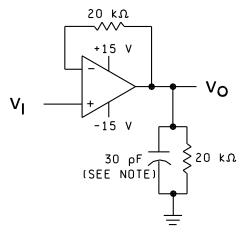
FIGURE 1. <u>Terminal connections</u>.

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SLEW RATE



SINGLE SUPPLY



SPLIT SUPPLY

NOTE: C_L includes fixture capacitance.

FIGURE 2. Test circuits.

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3.10 <u>Microcircuit group assignment for device class M</u>. Device class M devices covered by this drawing shall be in microcircuit group number 49 (see MIL-PRF-38535, appendix A).

4. QUALITY ASSURANCE PROVISIONS

- 4.1 <u>Sampling and inspection</u>. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.
- 4.2 <u>Screening</u>. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.
 - 4.2.1 Additional criteria for device class M.
 - a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition B or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
 - (2) $T_{\Delta} = +125^{\circ} \text{ C}$, minimum.
 - b. Interim and final electrical test parameters shall be as specified in table II herein.
 - 4.2.2 Additional criteria for device classes Q and V.
 - a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
 - b. Interim and final electrical test parameters shall be as specified in table II herein.
 - c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.
- 4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).
- 4.4 <u>Conformance inspection</u>. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-PRF-38535 permits alternate in-line control testing. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).
 - 4.4.1 Group A inspection.
 - a. Tests shall be as specified in table II herein.
 - b. Subgroups 7, 8, 9, 10, and 11 in table I, method 5005 of MIL-STD-883 shall be omitted.

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TABLE II. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgr (in accorda MIL-PRF-38	ance with
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)	1		1
Final electrical parameters (see 4.2)	1,2,3,4 <u>1</u> /	1,2,3,4 <u>1</u> /	1,2,3,4 <u>1</u> /
Group A test requirements (see 4.4)	1,2,3,4,5,6	1,2,3,4,5,6	1,2,3,4,5,6
Group C end-point electrical parameters (see 4.4)	1	1	
Group D end-point electrical parameters (see 4.4)	1	1	1
Group E end-point electrical parameters (see 4.4)	1,4	1,4	1,4

^{1/} PDA applies to subgroup 1 with exception of V_{IO}.

- 4.4.2 <u>Group C inspection</u>. The group C inspection end-point electrical parameters shall be as specified in table II herein.
- 4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:
 - a. Test condition B or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
 - b. $T_A = +125^{\circ}C$, minimum.
 - c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.
- 4.4.2.2 <u>Additional criteria for device classes Q and V.</u> The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
 - 4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table II herein.

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- 4.4.4 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).
 - a. End-point electrical parameters shall be as specified in table II herein.
 - b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T_A = +25°C ±5°C, after exposure, to the subgroups specified in table II herein.
 - c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.
 - 5. PACKAGING
- 5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.
 - 6. NOTES
- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
 - 6.1.2 Substitutability. Device class Q devices will replace device class M devices.
- 6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-973 using DD Form 1692, Engineering Change Proposal.
- 6.3 <u>Record of users</u>. Military and industrial users should inform Defense Supply Center Columbus when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0525.
- 6.4 <u>Comments</u>. Comments on this drawing should be directed to DSCC-VA, Columbus, Ohio 43216-5000, or telephone (614) 692-0674.
- 6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.
 - 6.6 Sources of supply.
- 6.6.1 <u>Sources of supply for device classes Q and V</u>. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.
- 6.6.2 <u>Approved sources of supply for device class M.</u> Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

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STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 96-10-08

Approved sources of supply for SMD 5962-90881 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535.

Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /
5962-9088101MGX	<u>3</u> /	TLE2021MLB
5962-9088101MPX	01295	TLE2021MJGB
5962-9088101M2X	01295	TLE2021MFKB
5962-9088102MGX	<u>3</u> /	TLE2022MLB
5962-9088102MPX	01295	TLE2022MJGB
5962-9088102M2X	01295	TLE2022MFKB
5962-9088103MCX	01295	TLE2024MJGB
5962-9088103M2X	01295	TLE2024MFKB
5962-9088104QPA	01295	TLE2021AMJGB
5962-9088104Q2A	01295	TLE2021AMFKB
5962-9088105QPA	01295	TLE2022AMJGB
5962-9088105Q2A	01295	TLE2022AMFKB
5962-9088106QCA	01295	TLE2024AMJB
5962-9088106Q2A	01295	TLE2024AMFKB

Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /
5962-9088107QPA	01295	TLE2021BMJGB
5962-9088107Q2A	01295	TLE2021BMFKB
5962-9088108QPA	01295	TLE2022BMJGB
5962-9088108Q2A	01295	TLE2022BMFKB
5962-9088109QCA	01295	TLE2024BMJB
5962-9088109Q2A	01295	TLE2024BMFKB

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. The device manufacturers listed herein are authorized to supply alternate lead finishes "A", "B", or "C" at their discretion. Contact the listed approved source of supply for further information.
- 2/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.
- 3/ Not available from an approved source of supply.

Vendor CAGEVendor namenumberand address

01295 Texas Instruments, Incorporation

13500 N. Central Expressway

P.O. Box 655303 Dallas, TX 75265

Point of contact: I-20 at FM 1788

Midland, TX 79711-0448